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APPLICATION NO. FILING DATE		ING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/719,943 11/21/2003		1/21/2003	Philip V. Pesavento	260385.20004	3523	
26418	6418 7590 12/20/2004 EXAMINER					
REED SMI	•	ORDS DEPAR	ERDEM, FAZLI			
	_	ENUE, 29TH F		ART UNIT	PAPER NUMBER	
NEW YORK		•		2826		
				DATE MAILED: 12/20/2004		

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)					
				PESAVENTO, PHILIP V.				
	Office Action Summary	10/719,943						
	omeorienen cummury	Examiner	Art Unit	الهور ا				
	The MAILING DATE of this communicate	Fazli Erdem	2826	ddross				
Period fo		on appears on the cover sneed	, with the correspondence at	Juless				
THE - Exte after - If the - If NC - Failt Any	ORTENED STATUTORY PERIOD FOR MAILING DATE OF THIS COMMUNICA' nsions of time may be available under the provisions of 37 SIX (6) MONTHS from the mailing date of this communicate or period for reply specified above is less than thirty (30) day of period for reply is specified above, the maximum statutor tree to reply within the set or extended period for reply will, the reply received by the Office later than three months after the patent term adjustment. See 37 CFR 1.704(b).	FION. CFR 1.136(a). In no event, however, may ation. It is, a reply within the statutory minimum of by period will apply and will expire SIX (6) Now statute, cause the application to become	y a reply be timely filed thirty (30) days will be considered time MONTHS from the mailing date of this of e ABANDONED (35 U.S.C. § 133).					
Status								
1)⊠	Responsive to communication(s) filed or	n <u>15 November 2004</u> .						
2a)□	This action is FINAL . 2b)	This action is non-final.						
3)□								
	closed in accordance with the practice u	inder <i>Ex parte Quayie</i> , 1935 C	J.D. 11, 453 O.G. 213.					
Disposit	ion of Claims							
5)□	Claim(s) <u>1-32</u> is/are pending in the appli 4a) Of the above claim(s) <u>32</u> is/are withd Claim(s) is/are allowed. Claim(s) <u>1-31</u> is/are rejected. Claim(s) is/are objected to. Claim(s) are subject to restriction	rawn from consideration.						
Applicat	ion Papers							
9)[The specification is objected to by the Ex	aminer.						
10)	10)☐ The drawing(s) filed on is/are: a)☐ accepted or b)☐ objected to by the Examiner.							
	Applicant may not request that any objection		•					
11)	Replacement drawing sheet(s) including the The oath or declaration is objected to by	•	• • •	` '				
Priority ı	ınder 35 U.S.C. § 119							
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received.								
Attachmen	t(s)							
	e of References Cited (PTO-892)		w Summary (PTO-413)					
3) 🛛 Infori	e of Draftsperson's Patent Drawing Review (PTO-9 nation Disclosure Statement(s) (PTO-1449 or PTO r No(s)/Mail Date <u>112103 and 110504</u> .		No(s)/Mail Date of Informal Patent Application (PT0 	O-152)				

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DETAILED ACTION

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 1-4 rejected under 35 U.S.C. 103(a) as being unpatentable over Stengel et al. (2003/0034505) in view of Aoyama et al. (JP 10218696).

Regarding Claims 1-4, Stengel et al. disclose a structure and method for fabricating semiconductor structures and devices utilizing the formation of a compliant substrate including an isotopically enriched material where in Fig. 9-12 it is disclosed isotopically enriched monocrystalline oxide material. Stengel et al. fail to disclose the oxide material to be piezoelectric type. However, Aoyama discloses multi-component-based ceramic material and perovskite-type PZT crystal where the PZT crystal is piezoelectric material.

It would have been obvious to one of having ordinary skill in the art at the time the invention was made to include the required piezoelectric material in Stengel at al. as taught by Aoyama et al. in order to have a semiconductor device with increased functionality.

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3. Claims 5-8 rejected under 35 U.S.C. 103(a) as being unpatentable over Stengel et al. (2003/0034505) in view of Aoyama et al. (JP 10218696) further in view of Burden (2004/0171226).

Regarding Claims 5-8, Stengel et al. disclose a structure and method for fabricating semiconductor structures and devices utilizing the formation of a compliant substrate including an isotopically enriched material where in Fig. 9-12 it is disclosed isotopically enriched monocrystalline oxide material. Stengel et al. fail to disclose the oxide material to be piezoelectric type and the Si28 type silicon isotope. However, Aoyama discloses multi-component-based ceramic material and perovskite-type PZT crystal where the PZT crystal is piezoelectric material. Furthermore, Burden discloses isotopically pure silicon-on-insulator wafer and method of making same where in claims section the required Si28 isotope is disclosed.

It would have been obvious to one of having ordinary skill in the art at the time the invention was made to include the required piezoelectric material and Si28 isotope in Stengel at al. and as taught by Aoyama et al. and Burden respectively, in order to have a semiconductor device with increased functionality.

4. Claims 9-18 rejected under 35 U.S.C. 103(a) as being unpatentable over Stengel et al. (2003/0034505) in view of Aoyama et al. (JP 10218696) further in view of Kelsey et al. (2003/0039865)

Regarding Claims 9-18, Stengel et al. disclose a structure and method for fabricating semiconductor structures and devices utilizing the formation of a compliant

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substrate including an isotopically enriched material where in Fig. 9-12 it is disclosed isotopically enriched monocrystalline oxide material. Stengel et al. fail to disclose the oxide material to be piezoelectric type and the Si29 and Si30 type silicon isotopes. However, Aoyama discloses multi-component-based ceramic material and perovskite-type PZT crystal where the PZT crystal is piezoelectric material. Furthermore, Kelsey et al. disclose isotopically engineered optical materials where the required Si29 and Si30 isotopes are disclosed.

It would have been obvious to one of having ordinary skill in the art at the time the invention was made to include the required piezoelectric material and Si29 and Si30 isotopes in Stengel at al. and as taught by Aoyama et al. and Kelsey et al. respectively, in order to have a semiconductor device with increased functionality.

5. Claims 19-31 rejected under 35 U.S.C. 103(a) as being unpatentable over Stengel et al. (2003/0034505) in view of Aoyama et al. (JP 10218696) further in view of Mulligan et al. (6,805,946).

Regarding Claims 19-31, Stengel et al. disclose a structure and method for fabricating semiconductor structures and devices utilizing the formation of a compliant substrate including an isotopically enriched material where in Fig. 9-12 it is disclosed isotopically enriched monocrystalline oxide material. Stengel et al. fail to disclose the oxide material to be piezoelectric type and the required different type of devices. However, Aoyama discloses multi-component-based ceramic material and perovskite-type PZT crystal where the PZT crystal is piezoelectric material. Furthermore, Mulligan

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et al. disclose multi-functional composite structures where the required different types of devices are disclosed.

It would have been obvious to one of having ordinary skill in the art at the time the invention was made to include the required different types of devices in Stengel at al. and as taught by Aoyama et al. and Mulligan et al. respectively, in order to have a semiconductor device with increased functionality.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Fazli Erdem whose telephone number is (571) 272-1914. The examiner can normally be reached on M - F 8:00 - 5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on (571) 272-1915. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

FE

December 13, 2004

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